

AMENDMENTS TO THE SPECIFICATION

Please replace the third paragraph on page 5, lines 5-7 as shown below:

Mask 1 is ~~realised~~ realized with a layer of transparent quartz 3 and an over-layer of opaque chrome 4 on which the opening of the etch window 5 is defined for the ~~realisation~~ realization of the contact, by means of an incident luminous source 6 on said etch window 5.

Please replace the sixth paragraph on page 5, lines 12-13 as shown below:

Mask 2 is an attenuated phase shifting mask, also called Att.PSM, and uses a layer of partially transparent material ~~[[6]]~~ 7 in place of said chrome layer ~~[[3]]~~ 4.

Please replace the third full paragraph on page 6, lines 8-10 as shown below:

According to what is illustrated in said graph an axis of the x-coordinate indicating the dimension of the contact expressed in μm and an axis of the ordinates indicating ~~normalised~~ normalized intensity can be noted.

Please replace the paragraph beginning on page 6, line 24 through page 7, line 1 as shown below:

According to what is illustrated in said figure it can be noted that with the use of said masks consideration must be taken of the side lobe effect, because if a zero-order maximum diffraction 15 is associated with a ~~normalised~~ normalized transmission intensity of value 1, which defines the dimension of the contact, the result is obtained that the side lobe is given by the intensity corresponding to a one-order maximum diffraction 16 whose value results being equal to 0.047. Said one-order maximum is distributed around the contact following the two orthogonal directions, as previously illustrated schematically in Figure 3.